

- Designed for Complementary Use with the BD241 Series
- 40 W at 25°C Case Temperature
- 3 A Continuous Collector Current
- 5 A Peak Collector Current
- Customer-Specified Selections Available

TO-220 PACKAGE

Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BD242		-55		
Collector-emitter voltage (R_{BE} = 100 Ω)	BD242A	V	-70	V	
	BD242B	V_{CER}	-90	v	
	BD242C		-115		
	BD242		-45		
Collector-emitter voltage (I _C = -30 mA)	BD242A	W	-60	V	
	BD242B	V_{CEO}	-80		
	BD242C		-100		
Emitter-base voltage			-5	V	
Continuous collector current			-3	Α	
Peak collector current (see Note 1)	I _{CM}	-5	Α		
Continuous base current			-1	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			40	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W	
Unclamped inductive load energy (see Note 4)			32	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range	T _{stg}	-65 to +150	°C		
Lead temperature 3.2 mm from case for 10 seconds			250	°C	

NOTES: 1. This value applies for $t_p \le 0.3$ ms, duty cycle $\le 10\%$.

- 2. Derate linearly to 150°C case temperature at the rate of $0.32 \text{ W/}^{\circ}\text{C}$.
- 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.



electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA (see Note 5)	I _B = 0	BD242 BD242A BD242B BD242C	-45 -60 -80 -100			V
I _{CES}	Collector-emitter cut-off current	$V_{CE} = -55 \text{ V}$ $V_{CE} = -70 \text{ V}$ $V_{CE} = -90 \text{ V}$ $V_{CE} = -115 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD242 BD242A BD242B BD242C			-0.2 -0.2 -0.2 -0.2	mA
I _{CEO}	Collector cut-off current	V _{CE} = -30 V V _{CE} = -60 V	I _B = 0 I _B = 0	BD242/242A BD242B/242C			-0.3 -0.3	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0				-1	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = -4 V$ $V_{CE} = -4 V$	$I_C = -1 A$ $I_C = -3 A$	(see Notes 5 and 6)	25 10			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = -0.6 A	I _C = -3 A	(see Notes 5 and 6)			-1.2	V
V_{BE}	Base-emitter voltage	V _{CE} = -4 V	I _C = -3 A	(see Notes 5 and 6)			-1.8	V
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -0.5 A	f = 1 kHz	20			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -0.5 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			3.125	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = -1 A	$I_{B(on)} = -0.1 \text{ A}$	$I_{B(off)} = 0.1 A$		0.2		μs
t _{off}	Turn-off time	$V_{BE(off)} = 3.7 V$	$R_L = 20 \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		0.3		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs **COLLECTOR CURRENT** TCS632AH 1000 V_{CE} = -4 V = 25°C t_p = 300 μs, duty cycle < 2% = 80°C h_{FE} - DC Current Gain 100 10 -0.01 -0.1 -1.0 -10 I_c - Collector Current - A

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

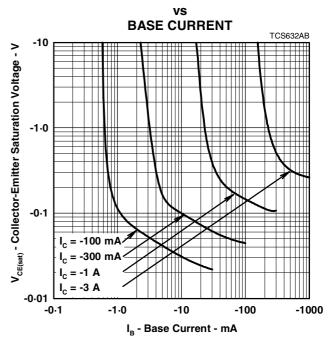
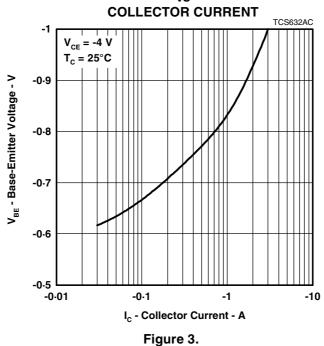
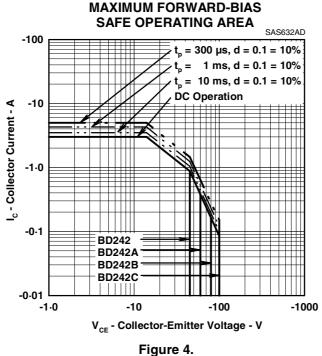


Figure 2.

BASE-EMITTER VOLTAGE



MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

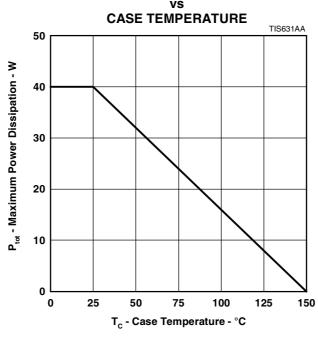


Figure 5.